Benjamin IÃ±iguez

List of Publications by Year
in descending order

179 papers	4,158 citations	126907 33 h-index	138484 58 g-index
179 all docs	179 docs citations	179 times ranked	2232 citing authors

#	Article	IF	Citations
1	Continuous Analytic I–V Model for Surrounding-Gate MOSFETs. IEEE Electron Device Letters, 2004, 25, 571-573.	3.9	254
2	Charge-Based Modeling of Junctionless Double-Gate Field-Effect Transistors. IEEE Transactions on Electron Devices, 2011, 58, 2628-2637.	3.0	218
3	Explicit Continuous Model for Long-Channel Undoped Surrounding Gate MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 1868-1873.	3.0	198
4	Accurate modeling and parameter extraction method for organic TFTs. Solid-State Electronics, 2005, 49, 1009-1016.	1.4	140
5	Compact model for short channel symmetric doped double-gate MOSFETs. Solid-State Electronics, 2008, 52, 1064-1070.	1.4	140
6	Modeling of Nanoscale Gate-All-Around MOSFETs. IEEE Electron Device Letters, 2004, 25, 314-316.	3.9	136
7	Analytical Model of the Threshold Voltage and Subthreshold Swing of Undoped Cylindrical Gate-All-Around-Based MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 572-579.	3.0	133
8	A short-channel DC SPICE model for polysilicon thin-film transistors including temperature effects. IEEE Transactions on Electron Devices, 1999, 46, 1146-1158.	3.0	117
9	Two-Dimensional Analytical Threshold Voltage and Subthreshold Swing Models of Undoped Symmetric Double-Gate MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 1402-1408.	3.0	99
10	Compact-Modeling Solutions For Nanoscale Double-Gate and Gate-All-Around MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 2128-2142.	3.0	91
11	Mobility model for compact device modeling of OTFTs made with different materials. Solid-State Electronics, 2008, 52, 787-794.	1.4	89
12	A Compact Model for Organic Field-Effect Transistors With Improved Output Asymptotic Behaviors. IEEE Transactions on Electron Devices, 2013, 60, 1136-1141.	3.0	85
13	Fully depleted SOI CMOS technology for heterogeneous micropower, high-temperature or RF microsystems. Solid-State Electronics, 2001, 45, 541-549.	1.4	81
14	Mobility behavior and models for fully depleted nanocrystalline ZnO thin film transistors. Solid-State Electronics, 2013, 90, 134-142.	1.4	71
15	Compact Charge-Based Physical Models for Current and Capacitances in AlGaN/GaN HEMTs. IEEE Transactions on Electron Devices, 2013, 60, 3746-3752.	3.0	70
16	Modeling of potentials and threshold voltage for symmetric doped double-gate MOSFETs. Solid-State Electronics, 2008, 52, 830-837.	1.4	62
17	Universal compact model for long- and short-channel Thin-Film Transistors. Solid-State Electronics, 2008, 52, 400-405.	1.4	61
18	A 3-D Analytical Physically Based Model for the Subthreshold Swing in Undoped Trigate FinFETs. IEEE Transactions on Electron Devices, 2007, 54, 2487-2496.	3.0	56

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19	A Quasi-Two-Dimensional Compact Drainâ€"Current Model for Undoped Symmetric Double-Gate MOSFETs Including Short-Channel Effects. IEEE Transactions on Electron Devices, 2008, 55, 1441-1448.	3.0	56
20	Self-heating and kink effects in a-Si:H thin film transistors. IEEE Transactions on Electron Devices, 2000, 47, 387-397.	3.0	54
21	Compact model for highly-doped double-gate SOI MOSFETs targeting baseband analog applications. Solid-State Electronics, 2007, 51, 655-661.	1.4	54
22	A physically-based C/sub â^ž/-continuous fully-depleted SOI MOSFET model for analog applications. IEEE Transactions on Electron Devices, 1996, 43, 568-575.	3.0	53
23	Threshold voltage, and 2D potential modeling within short-channel junctionless DG MOSFETs in subthreshold region. Solid-State Electronics, 2013, 90, 107-115.	1.4	52
24	Graphene electronic sensors â€" review of recent developments and future challenges. IET Circuits, Devices and Systems, 2015, 9, 446-453.	1.4	51
25	MIS polymeric structures and OTFTs using PMMA on P3HT layers. Solid-State Electronics, 2008, 52, 53-59.	1.4	50
26	RF and noise performance of double gate and single gate SOI. Solid-State Electronics, 2006, 50, 826-842.	1.4	46
27	Precise Modeling Framework for Short-Channel Double-Gate and Gate-All-Around MOSFETs. IEEE Transactions on Electron Devices, 2008, 55, 2678-2686.	3.0	45
28	Direct protein detection with a nano-interdigitated array gate MOSFET. Biosensors and Bioelectronics, 2009, 24, 3531-3537.	10.1	40
29	Effect of active layer thickness on the electrical characteristics of polymer thin film transistors. Organic Electronics, 2010, 11, 1920-1927.	2.6	38
30	Charge-based continuous model for long-channel Symmetric Double-Gate Junctionless Transistors. Solid-State Electronics, 2013, 85, 59-63.	1.4	37
31	Analytical modeling of bare surface barrier height and charge density in AlGaN/GaN heterostructures. Applied Physics Letters, 2012, 101, .	3.3	36
32	A Compact Explicit Model for Long-Channel Gate-All-Around Junctionless MOSFETs. Part I: DC Characteristics. IEEE Transactions on Electron Devices, 2014, 61, 3036-3041.	3.0	36
33	Analog performance of the nanoscale double-gate metal-oxide-semiconductor field-effect-transistor near the ultimate scaling limits. Journal of Applied Physics, 2004, 96, 5271-5276.	2.5	35
34	A simple compact model for long-channel junctionless Double Gate MOSFETs. Solid-State Electronics, 2013, 80, 28-32.	1.4	34
35	Noise modeling in fully depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 813-825.	1.4	33
36	Extraction method for polycrystalline TFT above and below threshold model parameters. Solid-State Electronics, 2002, 46, 2295-2300.	1.4	29

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37	Frequency and Voltage Dependence of the Capacitance of MIS Structures Fabricated With Polymeric Materials. IEEE Transactions on Electron Devices, 2013, 60, 2057-2063.	3.0	29
38	SOI n-MOSFET low-frequency noise measurements and modeling from room temperature up to 250Â°C. IEEE Transactions on Electron Devices, 2002, 49, 1289-1295.	3.0	28
39	Two-dimensional analytical threshold voltage roll-off and subthreshold swing models for undoped cylindrical gate all around MOSFET. Solid-State Electronics, 2006, 50, 805-812.	1.4	27
40	An analytical compact model for Schottky-barrier double gate MOSFETs. Solid-State Electronics, 2011, 64, 78-84.	1.4	27
41	A 2D closed form model for the electrostatics in hetero-junction double-gate tunnel-FETs for calculation of band-to-band tunneling current. Microelectronics Journal, 2014, 45, 1144-1153.	2.0	26
42	Analytical compact modeling framework for the 2D electrostatics in lightly doped double-gate MOSFETs. Solid-State Electronics, 2012, 69, 72-84.	1.4	25
43	Modeling and parameter extraction procedure for nanocrystalline TFTs. Solid-State Electronics, 2004, 48, 103-109.	1.4	24
44	The Equivalent-Thickness Concept for Doped Symmetric DG MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 2917-2924.	3.0	24
45	A compact model and direct parameters extraction techniques For amorphous gallium-indium-zinc-oxide thin film transistors. Solid-State Electronics, 2016, 126, 81-86.	1.4	24
46	Influence of P3HT:PCBM blend preparation on the active layer morphology and cell degradation. Microelectronics Reliability, 2011, 51, 597-601.	1.7	23
47	Effect of Density of States on Mobility in Small-Molecule n-Type Organic Thin-Film Transistors Based on a Perylene Diimide. IEEE Electron Device Letters, 2012, 33, 1201-1203.	3.9	23
48	Advances in Compact Modeling of Organic Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2020, 8, 1404-1415.	2.1	23
49	A physically based C/sub â̌/-continuous model for small-geometry MOSFET's. IEEE Transactions on Electron Devices, 1995, 42, 283-287.	3.0	22
50	Unified substrate current model for MOSFETs. Solid-State Electronics, 1997, 41, 87-94.	1.4	22
51	Conduction mechanisms of silicon oxide/titanium oxide MOS stack structures. Microelectronics Reliability, 2008, 48, 370-381.	1.7	22
52	Modeling the behavior of charge carrier mobility with temperature in thin-film polymeric transistors. Microelectronic Engineering, 2010, 87, 2565-2570.	2.4	22
53	A Compact Explicit Model for Long-Channel Gate-All-Around Junctionless MOSFETs. Part II: Total Charges and Intrinsic Capacitance Characteristics. IEEE Transactions on Electron Devices, 2014, 61, 3042-3046.	3.0	22
54	Charge based, continuous compact model for the channel current in organic thin-film transistors for all regions of operation. Solid-State Electronics, 2017, 133, 17-24.	1.4	22

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55	Compact model for long-channel cylindrical surrounding-gate MOSFETs valid from low to high doping concentrations. Solid-State Electronics, 2011, 55, 13-18.	1.4	21
56	Compact core model for Symmetric Double-Gate Junctionless Transistors. Solid-State Electronics, 2014, 94, 91-97.	1.4	21
57	Analytical Model for Schottky Barrier Height and Threshold Voltage of AlGaN/GaN HEMTs With Piezoelectric Effect. IEEE Transactions on Electron Devices, 2018, 65, 901-907.	3.0	21
58	An Improved C^∞-Continuous Small-Geometry MOSFET Modeling for Analog Applications. Analog Integrated Circuits and Signal Processing, 1997, 13, 241-259.	1.4	20
59	Analytical modeling of the gate tunneling leakage for the determination of adequate high-k dielectrics in double-gate SOI MOSFETs at the 22nm node. Solid-State Electronics, 2010, 54, 1083-1087.	1.4	20
60	Modeling the behavior of amorphous oxide thin film transistors before and after bias stress. Microelectronics Reliability, 2012, 52, 2532-2536.	1.7	20
61	DC self-heating effects modelling in SOI and bulk FinFETs. Microelectronics Journal, 2015, 46, 320-326.	2.0	20
62	Compact charge and capacitance modeling of undoped ultra-thin body (UTB) SOI MOSFETs. Solid-State Electronics, 2008, 52, 1867-1871.	1.4	19
63	2D analytical calculation of the electrostatic potential in lightly doped Schottky barrier Double-Gate MOSFET. Solid-State Electronics, 2010, 54, 1372-1380.	1.4	19
64	Compact model for short-channel symmetric double-gate junctionless transistors. Solid-State Electronics, 2015, 111, 196-203.	1.4	18
65	3-D compact model for nanoscale junctionless triple-gate nanowire MOSFETs, including simple treatment of quantization effects. Solid-State Electronics, 2015, 112, 85-98.	1.4	18
66	Compact drain-current model for undoped cylindrical surrounding-gate metal-oxide-semiconductor field effect transistors including short channel effects. Journal of Applied Physics, 2013, 114, .	2.5	17
67	A physically-based $C/sub\ \infty/$-continuous model for accumulation-mode SOI pMOSFETs. IEEE Transactions on Electron Devices, 1999, 46, 2295-2303.	3.0	16
68	Study of potential high-k dielectric for UTB SOI MOSFETs using analytical modeling of the gate tunneling leakage. Semiconductor Science and Technology, 2011, 26, 115002.	2.0	16
69	Analytical predictive modeling for the study of the scalability limits of multiple gate MOSFETs. Solid-State Electronics, 2007, 51, 414-422.	1.4	15
70	Implementation of the symmetric doped double-gate MOSFET model in Verilog-A for circuit simulation. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2010, 23, 88-106.	1.9	15
71	A physical compact DC drain current model for long-channel undoped ultra-thin body (UTB) SOI and asymmetric double-gate (DG) MOSFETs with independent gate operation. Solid-State Electronics, 2011, 57, 61-66.	1.4	15
72	Compact Modeling of Nonlinear Contact Effects in Short-Channel Coplanar and Staggered Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 3843-3850.	3.0	15

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73	DC SPICE model for nanocrystalline and microcrystalline silicon TFTs. IEEE Transactions on Electron Devices, 2002, 49, 1979-1984.	3.0	14
74	On the series resistance in staggered amorphous thin film transistors. Microelectronics Reliability, 2016, 63, 325-335.	1.7	14
75	Comments on "Threshold voltage model for deep-submicrometer MOSFETs. IEEE Transactions on Electron Devices, 1995, 42, 1712.	3.0	13
76	2D analytical calculation of the electric field in lightly doped Schottky barrier double-gate MOSFETs and estimation of the tunneling/thermionic current. Solid-State Electronics, 2011, 63, 119-129.	1.4	13
77	In-depth analysis and modelling of self-heating effects in nanometric DGMOSFETs. Solid-State Electronics, 2013, 79, 179-184.	1.4	13
78	Compact Capacitance Model for OTFTs at Low and Medium Frequencies. IEEE Transactions on Electron Devices, 2014, 61, 638-642.	3.0	13
79	Impact of the fringing capacitance at the back of thin-film transistors. Organic Electronics, 2011, 12, 936-949.	2.6	12
80	A compact explicit DC model for short channel Gate-All-Around junctionless MOSFETs. Solid-State Electronics, 2017, 131, 24-29.	1.4	12
81	Effect of interface charge on the dc bias stress-induced deformation and shift of the transfer characteristic of amorphous oxide thin-film transistors. Microelectronics Reliability, 2012, 52, 1342-1345.	1.7	11
82	A charge-based continuous model for submicron graded-channel nMOSFET for analog circuit simulation. Solid-State Electronics, 2005, 49, 1683-1692.	1.4	10
83	Optimized parameter extraction using fuzzy logic. Solid-State Electronics, 2007, 51, 683-690.	1.4	10
84	Stability of PMMA on P3HT PTFTs under stress. Solid-State Electronics, 2009, 53, 1063-1066.	1.4	10
85	Compact modeling solutions for short-channel SOI Schottky barrier MOSFETs. Solid-State Electronics, 2013, 82, 86-98.	1.4	10
86	Modeling of temperature effects in a surface-potential based ASM-HEMT model. , 2014, , .		10
87	An insight to mobility parameters for AOSTFTs, when the effect of both, localized and free carriers, must be considered to describe the device behavior. Solid-State Electronics, 2018, 149, 32-37.	1.4	10
88	A Complete Charge-Based Capacitance Model for IGZO TFTs. IEEE Electron Device Letters, 2019, 40, 730-733.	3.9	10
89	Charge-Based Compact Modeling of Capacitances in Staggered Multi-Finger OTFTs. IEEE Journal of the Electron Devices Society, 2020, 8, 396-406.	2.1	10
90	Modeling and performance study of nanoscale double gate junctionless and inversion mode MOSFETs including carrier quantization effects. Microelectronics Journal, 2014, 45, 1220-1225.	2.0	9

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91	Advanced analytical modeling of double-gate Tunnel-FETs – A performance evaluation. Solid-State Electronics, 2018, 141, 31-39.	1.4	9
92	CMOS radiation sensor with binary output. IEEE Transactions on Nuclear Science, 1995, 42, 174-178.	2.0	8
93	Modeling and simulation of single- and multiple-gate 2D MESFETs. IEEE Transactions on Electron Devices, 1999, 46, 1742-1748.	3.0	8
94	New numerical low frequency noise model for front and buried oxide trap density characterization in FDSOI MOSFETs. Microelectronic Engineering, 2011, 88, 1286-1290.	2.4	8
95	Analysis and Compact Modeling of Gate Capacitance in Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2019, 66, 2370-2374.	3.0	8
96	Charge-Based Model for the Drain-Current Variability in Organic Thin-Film Transistors Due to Carrier-Number and Correlated- Mobility Fluctuation. IEEE Transactions on Electron Devices, 2020, 67, 4667-4671.	3.0	8
97	New Compact Modeling Solutions for Organic and Amorphous Oxide TFTs. IEEE Journal of the Electron Devices Society, 2021, 9, 911-932.	2.1	8
98	A numerical study of scaling issues for trench power MOSFETs. Solid-State Electronics, 2005, 49, 965-975.	1.4	7
99	Electrical studies of semiconductor–dielectric interfaces. Journal of Materials Science: Materials in Electronics, 2006, 17, 663-683.	2.2	7
100	Temperature dependent compact modeling of gate tunneling leakage current in double gate MOSFETs. Solid-State Electronics, 2013, 81, 124-129.	1.4	7
101	Pseudo-Boltzmann model for modeling the junctionless transistors. Solid-State Electronics, 2014, 95, 19-22.	1.4	7
102	Crystalline-like temperature dependence of the electrical characteristics in amorphous Indium-Gallium-Zinc-Oxide thin film transistors. Solid-State Electronics, 2017, 135, 43-48.	1.4	7
103	$1/f$ noise analysis in high mobility polymer-based OTFTs with non-fluorinated dielectric. Applied Physics Letters, 2019, 114, .	3.3	7
104	Full capacitance model, considering the specifics of amorphous oxide semiconductor thin film transistors structures. Solid-State Electronics, 2019, 156, 16-22.	1.4	7
105	Compact Modeling of Short-Channel Effects in Staggered Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 5082-5090.	3.0	7
106	Physics-Based DC Compact Modeling of Schottky Barrier and Reconfigurable Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2022, 10, 416-423.	2.1	7
107	2D Analytical Calculation of the Parasitic Source/Drain Resistances in DG-MOSFETs Using the Conformal Mapping Technique. IETE Journal of Research, 2012, 58, 205.	2.6	6
108	Implementation of nanoscale double-gate CMOS circuits using compact advanced transport models. Microelectronics Journal, 2013, 44, 80-85.	2.0	6

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109	Analytical modeling of capacitances in tunnel-FETs including the effect of Schottky barrier contacts. Solid-State Electronics, 2019, 159, 191-196.	1.4	6
110	Current-voltage and flicker noise analysis and unified modeling for amorphous indium-gallium-zinc-oxide thin film transistors with etch stop layer from 298 to 333â€°K. Journal of Applied Physics, 2019, 125, .	2.5	6
111	Parameter Extraction and Compact Modeling of 1/f Noise for Amorphous ESL IGZO TFTs. IEEE Journal of the Electron Devices Society, 2020, 8, 407-412.	2.1	6
112	Flexible megahertz organic transistors and the critical role of the device geometry on their dynamic performance. Journal of Applied Physics, 2021, 130, .	2.5	6
113	Amorphous silicon carbide TFTs. Solid-State Electronics, 2006, 50, 460-467.	1.4	5
114	Reversible Electrical Characteristics in PMMA on P3HT OTFTs. ECS Transactions, 2007, 9, 383-388.	0.5	5
115	Compact capacitance modeling of a 3-terminal FET at zero drainâ€"source voltage. Solid-State Electronics, 2010, 54, 520-523.	1.4	5
116	Gate leakage current partitioning in nanoscale double gate MOSFETs, using compact analytical model. Solid-State Electronics, 2012, 75, 22-27.	1.4	5
117	Optimised design of an organic thin-film transistor amplifier using the gm/ID methodology. IET Circuits, Devices and Systems, 2012, 6, 136.	1.4	5
118	Performance Study of a Schottky Barrier Double-Gate MOSFET Using a Two-Dimensional Analytical Model. IEEE Transactions on Electron Devices, 2013, 60, 884-886.	3.0	5
119	An analytical 3D model for short-channel effects in undoped FinFETs. Journal of Computational Electronics, 2015, 14, 500-505.	2.5	5
120	Analytical Currentâ€"Voltage Model for Double-Gate a-IGZO TFTs With Symmetric Structure for Above Threshold. IEEE Transactions on Electron Devices, 2020, 67, 1980-1986.	3.0	5
121	Parameter Extraction and Compact Modeling of OTFTs From 150 K to 350 K. IEEE Transactions on Electron Devices, 2020, 67, 5685-5692.	3.0	5
122	Improved Direct Determination of MOSFET Saturation Voltage Using Fourier Techniques. IEEE Transactions on Electron Devices, 2004, 51, 2073-2077.	3.0	4
123	A simple model of the nanoscale double gate MOSFET based on the flux method. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3086-3089.	0.8	4
124	RF and Noise Performance of Multiple-Gate SOI MOSFETs. , 2006, , .		4
125	EFFECT OF PROCESS VARIATIONS ON AN OTFT COMPACT MODEL PARAMETERS. International Journal of High Speed Electronics and Systems, 2011, 20, 815-828.	0.7	4
126	Analytical modeling of surface-potential and drain current in AlGaAs/GaAs HEMT devices. , 2012, , .		4

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127	A compact charge-based physical model for AlGaN/GaN HEMTs. , 2013, , .		4
128	A charge-based capacitance model for AlGaAs/GaAs HEMTs. Solid-State Electronics, 2013, 82, 38-40.	1.4	4
129	Compact physical models for gate charge and gate capacitances of AlGaN/GaN HEMTs. , 2013, , .		4
130	Analytical temperature dependent model for nanoscale double-gate MOSFETs reproducing advanced transport models. Solid-State Electronics, 2014, 98, 2-6.	1.4	4
131	Experimentally verified drain€current model for variable barrier transistor. Electronics Letters, 2015, 51, 1364-1366.	1.0	4
132	Macromodel for AC and Transient Simulations of Organic Thin-Film Transistor Circuits Including Nonquasistatic Effects. IEEE Transactions on Electron Devices, 2020, 67, 4672-4676.	3.0	4
133	Equivalent DG Dimensions Concept for Compact Modeling of Short-Channel and Thin Body GAA MOSFETs Including Quantum Confinement. IEEE Transactions on Electron Devices, 2020, 67, 5381-5387.	3.0	4
134	Compact DC and Quasi-Static Capacitances Modeling of a-Si:H TFTs, Including Parasitic Capacitances. IEEE Transactions on Electron Devices, 2021, 68, 3384-3389.	3.0	4
135	Quasi-Compact Model of Direct Source-to-Drain Tunneling Current in Ultrashort-Channel Nanosheet MOSFETs by Wavelet Transform. IEEE Transactions on Electron Devices, 2022, 69, 17-24.	3.0	4
136	Cryogenic Temperature and Doping Analysis of Source-to-Drain Tunneling Current in Ultrashort-Channel Nanosheet MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1588-1595.	3.0	4
137	Compact RF Modeling of Multiple-Gate MOSFETs. , 2006, , .		3
138	Compact Modelling of Quantum Confinement in III-V Gate All Around Nanowire MOSFET. , 2018, , .		3
139	An analytical drain current model for cylindrical gate DMG-GC-DOT MOSFET. International Journal of Electronics Letters, 2019, 7, 458-472.	1.2	3
140	Direct Source-to-Drain Tunneling Current in Ultra-Short Channel DG MOSFETs by Wavelet Transform. , 2020, , .		3
141	Noise-Based Simulation Technique for Circuit-Variability Analysis. IEEE Journal of the Electron Devices Society, 2021, 9, 450-455.	2.1	3
142	Microwave Simulation on the Performance of High Power GaN/AlGaN Heterostructure Field Effect Transistors. Physica Status Solidi A, 1999, 176, 205-208.	1.7	2
143	Effect of localized traps on the anomalous behavior of the transconductance in nanocrystalline TFTs. Microelectronics Reliability, 2005, 45, 1161-1166.	1.7	2
144	Modeling Of Thin Film Transistors with Non-Ideal Contacts. ECS Transactions, 2007, 8, 165-170.	0.5	2

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145	A compact charge-based physical model for AlGaN/GaN HEMTs. , 2013, , .		2
146	Modeling of low frequency noise in FD SOI MOSFETs. Solid-State Electronics, 2013, 90, 116-120.	1.4	2
147	A complete and Verilog-A compatible Gate-All-Around long-channel junctionless MOSFET model implemented in CMOS inverters. Microelectronics Journal, 2015, 46, 1069-1072.	2.0	2
148	Analytical high frequency GaN HEMT model for noise simulations. Semiconductor Science and Technology, 2017, 32, 125012.	2.0	2
149	Compact mole fraction-dependent modeling of I-V and C-V characteristics in Al $$_{x}$$ x Ga $$_{1-x}$$ 1 - x N/GaN HEMTs. Journal of Computational Electronics, 2018, 17, 224-229.	2.5	2
150	Compact modelling for quantum confinement for InGaAs nanowire gate all around MOSFET. Electronics Letters, 2018, 54, 1348-1350.	1.0	2
151	Equivalent Length Concept for Compact Modeling of Short-Channel GAA and DG MOSFETs. , 2019, , .		2
152	Non-Linear Output-Conductance Function for Robust Analysis of Two-Dimensional Transistors. IEEE Electron Device Letters, 2021, 42, 94-97.	3.9	2
153	Modeling the Short-Channel Effects in Coplanar Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2022, 69, 1099-1106.	3.0	2
154	Comment on â€œNew Currentâ€"Voltage Model for Surrounding-Gate Metal Oxide Semiconductor Field-Effect Transistorsâ€. Japanese Journal of Applied Physics, 2006, 45, 6057-6057.	1.5	1
155	Improved Compact Model for Symmetric Doped Double-Gate MOSFETs. ECS Transactions, 2007, 9, 47-56.	0.5	1
156	A Compact Quantum Model of Nanoscale Double-Gate MOSFET for RF and Noise Simulations. , 2007, , .		1
157	ELECTRICAL PROPERTIES OF P3HT (POLY [3-HEXYLTHIOPHENE])/n-TYPE CRYSTALLINE SILICON (n-c-Si) SOLAR CELLS. International Journal of High Speed Electronics and Systems, 2011, 20, 749-773.	0.7	1
158	CHARGE BEHAVIOR IN ORGANIC THIN FILM TRANSISTORS. International Journal of High Speed Electronics and Systems, 2011, 20, 727-748.	0.7	1
159	Complex 2D Electric Field Solution in Undoped Double-gate MOSFETs. IETE Journal of Research, 2012, 58, 197.	2.6	1
160	A compact charge-based physical model for AlGaN/GaN HEMTs. , 2013, , .		1
161	Characterization of MIS structures and PTFTs using TiOx deposited by spin-coating. Microelectronics Reliability, 2014, 54, 893-898.	1.7	1
162	Accurate semi empirical predictive model for doped and undoped double gate MOSFET. Solid-State Electronics, 2018, 149, 23-31.	1.4	1

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163	Analytical Model for Threshold-Voltage Shift in Submicron Staggered Organic Thin-Film Transistors. , 2019, , .		1
164	A Piecewise Approximation for Short-Channel "Extrinsic" MOSFET Drain Current Dependence on Drain-to-Source Bias Including Linear Triode, Linear Saturation and Asymptotic Saturation Regimes. ECS Transactions, 2019, 90, 101-112.	0.5	1
165	Features of the Nonlinear Harmonic Distortion in AOSTFTs. IEEE Transactions on Electron Devices, 2019, 66, 5177-5182.	3.0	1
166	Dynamic Simulation of a-IGZO TFT Circuits Using the Analytical Full Capacitance Model (AFCM). IEEE Journal of the Electron Devices Society, 2021, 9, 464-468.	2.1	1
167	Deep-submicron drain current to radio frequency silicon on insulator metal oxide semiconductor field-effect transistor macromodel for designing microwave circuits. International Journal of RF and Microwave Computer-Aided Engineering, 2002, 12, 428-438.	1.2	0
168	Câ̌ž-continuous high-temperature model for low-doped accumulation mode silicon-on-insulator pMOSFETs. Solid-State Electronics, 2006, 50, 1261-1268.	1.4	0
169	A CAD model of Nanoscale Double-Gate MOSFET for RF and Noise applications including quantum and non-stationary effects. , 2007, , .		0
170	Compact model of output conductance in nanoscale bulk MOSFET based on 2D analytical calculations. Solid-State Electronics, 2008, 52, 1722-1729.	1.4	0
171	Automatic parameter extraction technique for gate leakage current modeling in double gate MOSFET. Solid-State Electronics, 2013, 89, 111-115.	1.4	0
172	A compact charge-based physical model for AlGaN/GaN HEMTs. , 2013, , .		0
173	A compact charge-based physical model for AlGaN/GaN HEMTs. , 2013, , .		0
174	COMPACT MODELING OF DOUBLE AND TRI-GATE MOSFETs. International Journal of High Speed Electronics and Systems, 2013, 22, 1350004.	0.7	0
175	Foreword Special Issue on Compact Modeling of Emerging Devices. IEEE Transactions on Electron Devices, 2014, 61, 221-224.	3.0	0
176	A quantum wave based compact modeling approach for the current in ultra-short DG MOSFETs suitable for rapid multi-scale simulations. Solid-State Electronics, 2017, 137, 70-79.	1.4	0
177	Foreword Special Issue on Compact Modeling of Semiconductor Devices. IEEE Journal of the Electron Devices Society, 2020, 8, 1350-1353.	2.1	0
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